Technical Data
DIODE

DISCRETE SEMICONDUCTOR
INDUSTRIES

maximum ratings

Voltage, Reverse (VR)	125.0	V
Voltage, Reverse Peak (VRM)	150.0	V
Current at VR = OV (IO)		A
Current Average Rectified (IF)	0.2	A
Current Surge Peak (IFM)	0.6	A
Current, Surge (IFM) at tp = 1 µs	4.0	A
Max. Power Dissipation (PT) at TA = 25° C	0.5	W
Max. Thermal Resistance (Rth J-A)	300.0	°C/W
Max. Junction Temperature (TJ)	175.0	°C

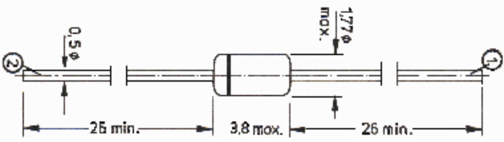
NO.	1N3595-M
TYPE	SILICON
CASE	DO-35
	MIL-S-19500
	BURN-IN 48h/125°C

PERFORMANCE CHARACTERISTICS at T_C = 25°C, unless otherwise noted

NO.	SYMBOL	CONDITIONS		MIN.	MAX.	UNITS
1.	VRM	IR = 100.0 µA	(1)	150.0	-	V
2.	IR	VR = 125.0 V		-	1.0	nA
3.	IR	VR = 125.0 V, TA = 150.0° C		-	3.0	µA
4.	VF	IF = 1.0 mA	(1)	0.52	0.68	V
5.	VF	IF = 5.0 mA	(1)	0.6	0.75	V
6.	VF	IF = 10.0 mA	(1)	0.65	0.8	V
7.	VF	IF = 50.0 mA	(1)	0.74	0.88	V
8.	VF	IF = 100.0 mA	(1)	0.79	0.92	V
9.	VF	IF = 200.0 mA	(1)	0.83	1.0	V
10.	CT	VR = 0 V, f = 1.0 MHz		-	8.0	pF
11.	trr	IF = 10.0 mA, VR = 35.0 V		-	3.0	ns
12.						
13.						
14.						
15.						
16.						
17.						
18.						
19.						
20.						

Notes (1)pulse-tested tp ≤ 300 µs, duty cycle ≤ 2 %

DIMENSIONS
in mm



Marking 3595-M + GREEN DOT

Customer GENERAL PURPOSE